Kinetic inductance of superconducting nanostrips with turns

Yasunori Mawatari¹

National Institute of Advanced Industrial Science and Technology (AIST), Tsukuba, Ibaraki 305–8568, Japan

(Dated: 12 May 2023)

Kinetic inductances of superconducting nanostrips with a meander pattern are theoretically investigated based on the London model, and the effect of the current crowding at the turns of the nanostrips is considered. The complex current approach is developed for analytical investigation of the kinetic inductance of nanostrips with turns for thin $d < \lambda$ and narrow $w \ll \lambda^2/d$ superconducting strips, where d is the strip thickness, w is the strip width, and λ is the London penetration depth. We show that the current distribution in superconducting nanostrips of $wd \ll \lambda^2/2$, where δ is the skin depth, and the dependence of the kinetic inductance on the nanostrip geometry is identical to that of the normal resistance. Effects of the edge defects of superconducting strips upon the kinetic inductance are also considered.

I. INTRODUCTION

Superconducting nanostrip single-photon detectors (SSPDs) have been extensively developed for applications in optical communications, quantum information, and optical quantum computing.¹ The reset time of SSPDs is proportional to the kinetic inductance of superconducting nanostrips,² which is a critical parameter for realizing SSPDs with a fast response. The kinetic inductance is crucial in microwave kinetic inductance detectors.³ In single flux quantum (SFQ) circuits, the implementation of the kinetic inductors can considerably reduce the area occupied by the cell inductors.⁴

Typical SSPDs are fabricated by patterning superconducting films with meander nanostrips with many turns, and Clem *et al.*^{5,6} theoretically investigated the effects of current crowding on the critical currents of superconducting nanostrips with turns. However, the current crowding effects on the kinetic inductance have not yet been clarified. Although it is possible to numerically estimate the kinetic inductance, simple analytical formulas are useful in the early stage of designing superconducting electronic devices.

In this paper, we theoretically investigate the twodimensional current distribution and kinetic inductance of superconducting nanostrips with meandering turns. This paper is organized as follows: basic equations based on the London model for analyzing the current distribution and kinetic inductance are shown in Sec. II; analytical expressions for the current distribution and the kinetic inductance of meander superconducting nanostrips are derived in Sec. III; and our results are summarized in Sec. IV.

II. BASIC EQUATIONS FOR SUPERCONDUCTING NANOSTRIPS

A. Kinetic inductance based on the London model

The London model is valid for superconductors of $\lambda/\xi \gg 1$, where λ is the London penetration depth and ξ is the coherence length. The London free energy $F_{\text{London}} = F_{\text{m}} + F_{\text{k}}$ is composed of the magnetic energy, $F_{\text{m}} = \int (|\boldsymbol{B}|^2/2\mu_0) dV$, and the kinetic energy, $F_{\text{k}} = \int (\mu_0 \lambda^2 |\boldsymbol{J}|^2/2) dV$, where \boldsymbol{B} is

the magnetic field, J is the current density, and μ_0 is the vacuum permeability. For a superconductor carrying transport current I_0 , the magnetic and kinetic energy can be rewritten as $F_{\rm m} = L_{\rm m} I_0^2/2$ and $F_{\rm k} = L_{\rm k} I_0^2/2$, respectively, where $L_{\rm m}$ is the magnetic inductance and $L_{\rm k}$ is the kinetic inductance.⁷⁻¹⁰

In this paper, we investigate thin superconducting nanostrips of thickness *d* and width *w* in the *xy*-plane, where $d < \lambda$ and $w \ll \lambda^2/d$. In these thin narrow strips, kinetic energy is dominant, $F_{\text{London}} \simeq F_k \gg F_m$, and the kinetic inductance is dominant, $L_0 \simeq L_k \gg L_m$. Thus, we consider the kinetic inductance (in units of [H]) of superconducting nanostrips defined by

$$L_{\rm k} = \frac{\mu_0 \lambda^2}{I_0^2} \int |\mathbf{J}|^2 dV = \frac{\mu_0 \lambda^2 d}{I_0^2} \iint \left(J_x^2 + J_y^2\right) dx dy, \quad (1)$$

where J_x and J_y are the components of the current density in the *xy*-plane. For a straight nanostrip with no turns of thickness *d* and width *w*, the current density is uniform, $J_x = I_0/wd$ and $J_y = 0$, and the kinetic inductance, $L_k = L_{k0}$, calculated from Eq. (1) is given by

$$L_{\rm k0} = \frac{\mu_0 \lambda^2}{d} \frac{\ell_0}{w},\tag{2}$$

where ℓ_0 is the length of a straight nanostrip.

B. Normal resistance and kinetic inductance

The dissipation power of superconducting nanostrips in the normal state is given by $R_n I_0^2 = \int \rho_n |J|^2 dV$, where R_n is the normal resistance (in units of $[\Omega]$) and ρ_n is the normal resistivity of nanostrips. Thus, the normal resistance is given by

$$R_{\rm n} = \frac{\rho_{\rm n}}{I_0^2} \int |\mathbf{J}|^2 dV = \frac{\rho_{\rm n} d}{I_0^2} \iint \left(J_x^2 + J_y^2\right) dx dy.$$
(3)

Although the expression $L_k/\mu_0\lambda^2 = \int |\boldsymbol{J}/I_0|^2 dV$ of Eq. (1) is similar to $R_n/\rho_n = \int |\boldsymbol{J}/I_0|^2 dV$ of Eq. (3), the volume integral of $\int |\boldsymbol{J}/I_0|^2 dV$ in superconductors does not necessarily

coincide with that in normal conductors. As shown in Appendix A, however, the current distribution in superconducting nanostrips of $wd \ll \lambda^2$ is identical to that in normal conducting nanostrips of $wd \ll \delta^2/2$, where δ is the skin depth. The volume integral $\int |J/I_0|^2 dV$ for such nanostrips is determined by the geometry of nanostrips and is independent of the material parameters.

Equations (1) and (3) are, therefore, rewritten as

$$\frac{L_{\rm k}}{\mu_0 \lambda^2} = \frac{R_{\rm n}}{\rho_{\rm n}},\tag{4}$$

which means that the kinetic inductance is proportional to the normal resistance, regardless of the geometrical structure of the superconducting nanostrips. Equation (4) has already been suggested in Refs. 2 and 8 without careful consideration of the identity of the current distribution in superconductors and that in normal conductors.

Hall¹¹ theoretically investigated the normal resistance of thin-film patterns (i.e., strips with turns) of various geometries. Most of the results of the normal resistance shown in Ref. 11 are expressed as the general form, $R_n = (\rho_n/d)[(\ell_0/w) + \alpha]$, where α is a numerical factor arising from the effect of turns.

Because of the proportional relationship, $L_k \propto R_n$, in Eq. (4), analytical formulas for L_k of superconducting nanostrips are simply obtained by converting the formulas for R_n listed in Ref. 11, as suggested by Tolpygo *et al.*^{12,13} Some of the L_k formulas for typical geometries are listed in the Appendix B. The general expression of the kinetic inductance for $\ell_0 \gg w$ is also given by

$$L_{\rm k} = \frac{\mu_0 \lambda^2}{d} \left(\frac{\ell_0}{w} + \alpha \right),\tag{5}$$

which is similar to Eq. (2) for straight strips, although correction factor α arises from the effect of turns. Numerical factor α in Eq. (5) depends on the geometry of the turns of nanostrips and tends to be large when the current crowding effect is large.

C. Complex current density and kinetic inductance

We investigate the two-dimensional current density, $J = J_x(x,y)\hat{x} + J_y(x,y)\hat{y}$, in the *xy*-plane based on the London model, by using the complex current approach.^{5,6,11,14}

The current density is solenoidal, $\nabla \cdot J = 0$, because of Ampère's law, $J = \nabla \times B/\mu_0$, and we have $J = \nabla \times (\psi \hat{z})$, where $\psi(x, y)$ is a scalar function. The London equation in superconductors without vortices, $\nabla \times J = -B/\mu_0 \lambda^2$, can be approximated as $\nabla \times J = 0$ for nanostrips of $w \ll \lambda^2/d$ with no applied magnetic field, as shown in Appendix A, and we have $J = -\nabla \varphi$, where $\varphi(x, y)$ is a scalar function. This approximation is consistent with the neglect of the magnetic energy, as in Sec. II. A. See Ref. 15 for a precise numerical investigation considering the magnetic energy.

The two-dimensional current density is, therefore, expressed as

$$J_x = \partial \psi / \partial y = -\partial \varphi / \partial x, \tag{6}$$

$$J_{y} = -\partial \psi / \partial x = -\partial \varphi / \partial y.$$
(7)

Equations (6) and (7) correspond to the Cauchy–Riemann conditions¹⁶ for ψ and φ . Therefore, complex stream function \mathscr{G} and complex current \mathscr{J} defined by

$$\mathscr{G} = \psi + i\varphi, \tag{8}$$

$$\mathscr{J} = J_y + iJ_x = -d\mathscr{G}/d\zeta \tag{9}$$

are analytic functions of complex variable $\zeta = x + iy$. The streamlines of the current density correspond to the contour lines of $\psi = \text{Re}\mathcal{G}$. As shown in Appendix C, transport current I_0 and kinetic inductance L_k defined by Eq. (1) are related to ψ and φ by

$$I_0/d = \psi_2 - \psi_1, \tag{10}$$

$$L_k I_0 / \mu_0 \lambda^2 = \varphi_2 - \varphi_1, \qquad (11)$$

where ψ_1 and ψ_2 are the values of ψ at the sides and φ_1 and φ_2 are the values of φ at the ends of the nanostrips.

III. MEANDER SUPERCONDUCTING NANOSTRIPS

In this section, we investigate the current distribution and kinetic inductance of meander superconducting nanostrips. The formulas presented in this section are similar to those for magnetic field distribution and effective permeability of a hexagonal array of superconducting strips.^{17,18}

A. Current distribution in meander nanostrips

We investigate a model of meander superconducting nanostrips, the geometry of which is shown in Fig. 1 (a). Because of the periodic structure along the *y*-direction, it is sufficient to consider a unit cell of length ℓ_0 and width *w* (i.e., $0 < x < \ell_0$ and 0 < y < w) [Fig. 1 (b)].

Here we introduce the conformal mapping from the $\zeta = x + iy$ -plane to the $\eta = u + iv$ -plane,^{17,18}

$$\eta(\zeta) = \operatorname{sn}(\zeta/c, k_1), \tag{12}$$

where $\operatorname{sn}(u,k)$ is the sine amplitude (i.e., the Jacobi sn function).¹⁹ Modulus k_1 in Eq. (12) is determined as the function of ℓ_0/w by solving

$$\frac{\ell_0}{w} = \frac{\mathbf{K}(k_1)}{\mathbf{K}\left(\sqrt{1-k_1^2}\right)},\tag{13}$$

where $\mathbf{K}(k)$ is the complete elliptic integral of the first kind.¹⁹ Parameter *c* in Eq. (12) is given by

$$c = \frac{\ell_0}{\mathbf{K}(k_1)} = \frac{w}{\mathbf{K}\left(\sqrt{1 - k_1^2}\right)}.$$
 (14)

The unit cell in the $\zeta = x + iy$ -plane, $0 < x < \ell_0$ and 0 < y < w, is mapped onto the first quadrant of the $\eta = u + iv$ -plane, u > 0 and v > 0.

Using the conformal mapping technique, we obtain the complex current defined by Eq. (9) as^{17,18}

$$\mathscr{J}(\zeta) = J_0 \frac{\eta \sqrt{\eta^2 - k_1^{-2}}}{\sqrt{(\eta^2 - \gamma^2)(\eta^2 - \beta^2)}},$$
(15)

where γ and β are defined by

$$\gamma = \eta(\ell_0 - s) = \operatorname{sn}((\ell_0 - s)/c, k_1),$$
 (16)

$$\beta = \eta (s + iw) = \sqrt{\frac{k_1^{-2} - \gamma^2}{1 - \gamma^2}}.$$
(17)

Parameter $J_0 = J_y(0, w)$ in Eq. (15) is the current density at (x, y) = (0, w), and J_0 is proportional to transport current I_0 , as shown below.

The complex stream function, $\mathscr{G} = \int_{iw}^{\zeta} \mathscr{J}(\zeta') d\zeta'$, is obtained by integrating Eq. (15) as

$$\mathscr{G}(\zeta) = \frac{cJ_0}{k_1} \int_{\eta}^{\infty} \frac{\eta' d\eta'}{\sqrt{(\eta'^2 - 1)(\eta'^2 - \beta^2)(\eta'^2 - \gamma^2)}} = \frac{cJ_0}{k_1\sqrt{\beta^2 - \gamma^2}} F\left(\arcsin\sqrt{\frac{\beta^2 - \gamma^2}{\eta^2 - \gamma^2}}, k_2\right), \quad (18)$$

where $F(\theta, k)$ is the elliptic integral of the first kind,¹⁹ and the



FIG. 1. Geometry of a meander superconducting nanostrip in the *xy*-plane. The thickness of the edges of the nanostrips (thick lines) is infinitesimal. (a) Periodic meander structure extended in the *y*-direction. The thick arrows show the schematic direction of the current flow. (b) Unit cell of $0 < x < \ell_0$ and 0 < y < w, where ℓ_0 is the strip length, *w* is the strip width, and *s* is the turn width. The variable transform of Eq. (12) maps the points $\zeta = 0$, $\ell_0 - s$, ℓ_0 , $\ell_0 + iw$, s + iw, and *iw* in the ζ -plane onto the points $\eta = 0$, γ , 1, $1/k_1$, β , and ∞ in the η -plane, respectively.

modulus, k_2 , is defined by

$$k_2 = \left[1 + \frac{k_1^{-2} - 1}{(1 - \gamma^2)^2}\right]^{-1/2}.$$
 (19)

Coefficient J_0 in Eqs. (15) and (18) is determined by Eq. (10) and (18) as

$$I_{0}/d = \psi(\ell_{0}, 0) - \psi(\ell_{0} - s, 0)$$

= Re [$\mathscr{G}(\ell_{0}) - \mathscr{G}(\ell_{0} - s)$]
= $\frac{cJ_{0}}{k_{1}} \int_{\gamma}^{1} \frac{udu}{\sqrt{(u^{2} - \gamma^{2})(1 - u^{2})(\beta^{2} - u^{2})}}$
= $\frac{cJ_{0}}{k_{1}\sqrt{\beta^{2} - \gamma^{2}}} \mathbf{K}(k_{2}).$ (20)

Figure 2 shows the streamlines of the current density, which correspond to the contour lines of $\psi(x, y) = \text{Re}\mathscr{G}(x+iy)$ obtained from Eq. (18).

B. Kinetic inductance of meander nanostrips

Here, we consider the kinetic inductance, L_k , for one unit cell of the superconducting nanostrips [Fig. 1(b)]. Using Eqs. (11) and (18), we have

$$L_{\mathbf{k}}I_{0}/\mu_{0}\lambda^{2} = \varphi(\ell_{0},0) - \varphi(s,w)$$

$$= \operatorname{Im}\left[\mathscr{G}(\ell_{0}) - \mathscr{G}(s+iw)\right]$$

$$= \frac{cJ_{0}}{k_{1}}\int_{1}^{\beta}\frac{udu}{\sqrt{(u^{2}-\gamma^{2})(u^{2}-1)(\beta^{2}-u^{2})}}$$

$$= \frac{cJ_{0}}{k_{1}\sqrt{\beta^{2}-\gamma^{2}}}\mathbf{K}\left(\sqrt{1-k_{2}^{2}}\right). \quad (21)$$

Substituting Eq. (20) into Eq. (21) yields the kinetic inductance,

$$L_{\mathbf{k}} = \frac{\mu_0 \lambda^2}{d} \frac{\mathbf{K}\left(\sqrt{1-k_2^2}\right)}{\mathbf{K}(k_2)}.$$
 (22)

Figure 3 shows the plot of L_k as functions of s/ℓ_0 obtained from Eqs. (22).

In Eqs (23)–(25), we demonstrate simple formulas for L_k as functions of turn width *s* for narrow strips of $w \ll \ell_0$. See Appendix D for the derivation of those equations.

$$L_{\rm k} \simeq \frac{\mu_0 \lambda^2}{d} \left[\frac{\ell_0}{w} + \frac{4}{\pi} \ln\left(\frac{2w}{\pi s}\right) \right] \quad \text{for } s \ll w, \tag{23}$$

$$L_{\rm k} \simeq \frac{\mu_0 \lambda^2}{d} \left[\frac{\ell_0 - 2s}{w} + \frac{4}{\pi} \ln(2) \right] \quad \text{for } w < s < \ell_0/2, \quad (24)$$

$$L_{\rm k} \simeq \frac{\mu_0 \lambda^2}{d} \left[\frac{2s - \ell_0}{w} + \frac{4}{\pi} \ln(2) \right]^{-1} \text{ for } \ell_0 / 2 < s < \ell_0.$$
 (25)

For the case where turn width s is much smaller than strip width w (i.e., $s \ll w$), current crowding occurs at the turns



FIG. 2. Streamlines of the current density in meander superconducting nanostrips of $w/\ell_0 = 0.2$ for (a) $s/\ell_0 = 0.1$ (s < w), (b) $s/\ell_0 = 0.3$ ($w < s < \ell_0/2$), and (c) $s/\ell_0 = 0.6$ ($s > \ell_0/2$). Thick lines correspond to the edges of the nanostrips.

[Fig. 2(a)], resulting in large kinetic inductance [Eq. (23) and Fig. 3]. For the most realistic case for SSPDs, $w < s < \ell_0/2$, current is not so crowded at the turns [Fig. 2(b)], and the effective strip length is given by $\ell_0 - 2s$ [Eq. (24) and the dashed line in Fig. 3]. We see a noticeable increase of L_k for $w/\ell_0 > 0.1$ especially for s < w, and Fig. 3 is useful to estimate L_k for devices using superconducting strips with $w/\ell_0 > 0.1$.

Although the case where $s > \ell_0/2$ is unrealistic for SSPDs, Eq. (25) is useful to consider the effects of the periodic edge defects in straight strips [i.e., a strip of width ℓ_0 with the notches of length $\ell_0 - s$ and of periodicity w, as seen in Fig. 2(c)]. The effective width of the current flow along the y axis is about $2s - \ell_0$, which is smaller than the actual width ℓ_0 , as seen in Eq. (25) for $\ell_0 - s \gg w$. For small-defect limit of $\ell_0 - s \ll w$, we have $L_k \simeq (\mu_0 \lambda^2/d)[(w/\ell_0) + (\pi/2)(1 - s/\ell_0)^2]$.



FIG. 3. Kinetic inductance L_k vs turn width *s* for $w/\ell_0 = 0.1, 0.2$, and 0.3. The dashed line corresponds to the limit of $w/\ell_0 \rightarrow 0$, $L_k = \mu_0 \lambda^2 (\ell_0 - 2s)/(wd)$. L_k and *s* are normalized by L_{k0} from Eq. (2) and ℓ_0 , respectively.

IV. DISCUSSION AND SUMMARY

On the basis of the London model, we theoretically investigate the current flow in superconducting nanostrips with meander turns, using the complex current approach and conformal mapping. The simple relationships between current, kinetic inductance, and the complex stream function given by Eqs. (10) and (11) are valid for any geometry of superconducting nanostrips and are useful for the analytical investigation of L_k for more complicated geometry.

In most long and narrow (i.e., $w \ll \ell_0$ and $w \ll \lambda^2/d$) superconducting nanostrips, the kinetic inductance is generally given by Eq. (5), and factor $\alpha \sim 1$ can be neglected when the current crowding is nonsignificant. Although the critical currents of superconducting nanostrips are strongly affected by the current crowding at turns,^{5,6} its effects can be neglected in the kinetic inductance.¹³ For superconducting devices with nanostrips of $w/\ell_0 > 0.1$ the current crowding effect on L_k is evident especially for s < w, as shown in Fig. 3.

The current distribution in superconducting nanostrips of $wd \ll \lambda^2$ is identical to that in normal conducting nanostrips of $wd \ll \delta^2/2$, when the conductor geometry is identical. Because of the proportional relationship between the normal resistance R_n of $wd \ll \delta^2/2$ and the kinetic inductance L_k of $wd \ll \lambda^2$, the analytical formulas of R_n for various geometries listed in Ref. 11 can be used to estimate L_k .

Equation (25) for $\ell_0/2 < s < \ell_0$ and $\ell_0 - s \gg w$ demonstrates the kinetic inductance of a straight strip of width ℓ_0 with edge defects of length $\ell_0 - s$ and of periodicity w. The edge defects of small periodicity $w \ll \ell_0 - s$ reduce the effective width $2s - \ell_0 (< \ell_0)$ of the current flow, resulting in the increase in the kinetic inductance.

The nonlinear microwave response of superconducting nanostrips and the quadratic current dependence of the kinetic inductance are also important problems in microwave applications of superconductors.^{3,20} We restrict the consideration to the case where the current is sufficiently smaller than the critical current and the liner London model is valid. The nonlinear response can be considered based on, for example, Ginzburg–Landau theory^{21–23} or microscopic theory.^{24–26} The theoretical investigation of the effects of turns in supercon-

ducting nanostrips on the nonlinear kinetic inductance will be addressed in future works.

Appendix A: Current density in nanostrips

We consider the response of superconducting nanostrips and of normal conducting nanostrips to the ac transport current with frequencies ranging from dc to at most microwave frequencies. We can safely disregard the displacement current in such a frequency regime, and Ampère's law without the displacement current $J = \nabla \times B/\mu_0$ reduces to $\nabla \cdot J = 0$.

In superconductors without an applied magnetic field, the current density follows the London equation given by $\nabla \times J = -B/\mu_0\lambda^2$, where the only magnetic field contribution is the self-field $B = B_1$ due to the transport current in strips. The solution of the London equation is given by $J = J_0 + J_1$, where J_0 is the solution neglecting the selffield, $\nabla \times J_0 = 0$, and J_1 is the contribution from the selffield, $\nabla \times J_1 = -B_1/\mu_0\lambda^2$. We estimate $|J_1|$ comparing $|J_0|$ by the perturbative calculation for $wd \ll \lambda^2$. The self-field due to J_0 is roughly estimated as $|B_1| \sim \mu_0 |J_0| d$,^{27,28} and we have $|J_1| \sim |B_1|w/\mu_0\lambda^2 \sim |J_0|wd/\lambda^2$, because $|\nabla \times J_1| \sim |J_1|/w$. We see that the contribution from the self-field $|J_1| \sim |J_0|wd/\lambda^2 \ll |J_0|$ can be neglected for $wd \ll \lambda^2$ in superconducting nanostrips.

In normal conductors with the normal resistivity ρ_n the current density $J = E/\rho_n$ follows the Faraday's law, $\nabla \times E = -\partial B/\partial t$ or $\nabla \times J = -(1/\rho_n)\partial B_1/\partial t$. The solution in normal conductors is also given by $J = J_0 + J_1$, where J_0 is the solution neglecting the self-field, and J_1 is the contribution from the self-field, $\nabla \times J_1 = -(1/\rho_n)\partial B_1/\partial t$. Because $|\partial B_1/\partial t| \sim \mu_0 \omega d |J_0|$, we estimate $|J_1| \sim |J_0|\mu_0 \omega w d/\rho_n = |J_0|2wd/\delta^2$, where ω is the angular frequency and $\delta = \sqrt{2\rho_n/\mu_0\omega}$ is the skin depth. The contribution from the self-field $|J_1| \sim |J_0|2wd/\delta^2 \ll |J_0|$ can be neglected for $wd \ll \delta^2/2$ in normal conducting nanostrips.

The current density follows $\nabla \times J = 0$ neglecting the selffield effect in superconducting nanostrips of $wd \ll \lambda^2$ and also in normal conducting nanostrips of $wd \ll \delta^2/2 = \rho_n/\mu_0 \omega$. The current density following $\nabla \times J = 0$ and $\nabla \cdot J = 0$ is simply obtained as $J = -\nabla \varphi$ by solving $\nabla^2 \varphi = 0$ with boundary conditions. We, thus, come to the conclusion that the current density in superconducting nanostrips of $wd \ll \lambda^2$ is identical to that in normal conducting nanostrips of $wd \ll \delta^2/2$, provided that the nanostrip geometry is identical.

Appendix B: Kinetic inductance for nanostrips with turns

Here, we demonstrate analytical formulas of L_k for several superconducting nanostrip geometries. These formulas are simply obtained by using Eq. (4) and converting from the formulas of the normal resistance R_n presented in Ref. 11.

For a superconducting nanostrip with a 90° turn [Fig. 4(a)], kinetic inductance is given by Eq. (5) with

$$\alpha = -1 - (2/\pi)\ln 2 = -1.44. \tag{B1}$$

For a superconducting nanostrip with a 180° turn [Fig. 4(b)], kinetic inductance is given by Eq. (5) as

$$\alpha = -\frac{4}{\pi} \ln \left[\sinh \left(\frac{\pi s}{2w} \right) \right], \tag{B2}$$

which is identical to Eq. (D9).

For a superconducting nanostrip with a thin vertical notch of length a [Fig. 4(c)], kinetic inductance is given by Eq. (5) as

$$\alpha = -\frac{4}{\pi} \ln \left[\cos \left(\frac{\pi a}{2w} \right) \right]. \tag{B3}$$

Appendix C: Transport current, kinetic inductance, and stream function

Because the normal component of the current density vanishes at the sides of a nanostrip, we have $\boldsymbol{J} \cdot \hat{\boldsymbol{n}} = \nabla \times (\boldsymbol{\psi} \hat{\boldsymbol{z}}) \cdot \hat{\boldsymbol{n}} = (\hat{\boldsymbol{z}} \times \hat{\boldsymbol{n}}) \cdot \nabla \boldsymbol{\psi} = 0$, which means that the tangential differentiation of $\boldsymbol{\psi}$ at the sides is zero. Thus, we obtain the boundary conditions of constant $\boldsymbol{\psi}$ at the sides, $\boldsymbol{\psi} = \boldsymbol{\psi}_1$ at one side and $\boldsymbol{\psi} = \boldsymbol{\psi}_2$ at the other side of a nanostrip, where $\boldsymbol{\psi}_1$ and $\boldsymbol{\psi}_2$ are constants.

If the current density is normal to the ends of a nanostrip, where a transport current flows in or out, then we have $J \cdot (\hat{n} \times \hat{z}) = -\nabla \varphi \cdot (\hat{n} \times \hat{z}) = 0$, which means that the tangential differentiation of φ at the ends is zero. Consequently, we obtain the boundary conditions of constant φ at the ends, of $\varphi = \varphi_1$ at one end and $\varphi = \varphi_2$ at the other end of a nanostrip, where φ_1 and φ_2 are constants.

The net sheet current, I_0/d , is calculated as the line integral of the normal component of the current density at the ends,

$$\frac{I_0}{d} = \int \boldsymbol{J} \cdot \hat{\boldsymbol{n}} \, d\boldsymbol{s} = \int \nabla \boldsymbol{\psi} \cdot (\hat{\boldsymbol{z}} \times \hat{\boldsymbol{n}}) d\boldsymbol{s} = \int \nabla \boldsymbol{\psi} \cdot d\boldsymbol{s}, \quad (C1)$$

and we obtain Eq. (10).

Green's theorem in the *xy*-plane,²⁹

$$\iint \left(\frac{\partial Q}{\partial x} - \frac{\partial P}{\partial y}\right) dx dy = \oint (P dx + Q dy), \quad (C2)$$



FIG. 4. Superconducting nanostrips of length ℓ_0 and width *w* with (a) a 90° turn, (b) a 180° turn of turn width *s*, and (c) a thin vertical notch of length *a*.

with $P = \psi \partial \varphi / \partial x$ and $Q = \psi \partial \varphi / \partial y$ leads to

$$\iint \left(\frac{\partial \psi}{\partial x}\frac{\partial \varphi}{\partial y} - \frac{\partial \psi}{\partial y}\frac{\partial \varphi}{\partial x}\right)dxdy = \oint \psi \left(\frac{\partial \varphi}{\partial x}dx + \frac{\partial \varphi}{\partial y}dy\right).$$
(C3)

Substitution of Eqs. (6) and (7) into the left-hand side of Eq. (C3) yields

$$\iint \left(J_x^2 + J_y^2\right) dx dy = \oint \psi d\varphi.$$
 (C4)

Because ψ is constant at the sides and φ is constant at the ends of nanostrips, the right-hand side of Eq. (C4) reduces to

$$\iint (J_x^2 + J_y^2) \, dx dy = (\psi_2 - \psi_1) \int d\varphi = (\psi_2 - \psi_1)(\varphi_2 - \varphi_1),$$
(C5)

where φ_1 and φ_2 are the values of φ at the ends of nanostrips. Equation (C5) can also be readily derived from

$$\iint \left| \frac{d\mathscr{G}}{d\zeta} \right|^2 dx dy = \iint d\varphi d\psi, \tag{C6}$$

where $|d\mathscr{G}/d\zeta|^2 = J_x^2 + J_y^2$ corresponds to the Jacobian²⁹ of the variable transform from (x, y) to (ψ, φ) . Substitution of Eqs. (10) and (C5) into Eq. (1) yields Eq. (11).

Appendix D: Simplified expressions of the kinetic inductance of meander nanostrips

Here, we derive simplified expressions for L_k given by Eqs. (23), (24), and (25) from Eq. (22) with Eqs. (13), (14), (16), and (19).

Equation (22) for
$$k_2 \ll 1$$
 or $k'_2 = \sqrt{1 - k_2^2} \ll 1$ reduces to

$$L_{\rm k} \simeq \frac{\mu_0 \lambda^2}{d} \frac{2}{\pi} \ln\left(\frac{4}{k_2}\right) \qquad \text{for } k_2 \ll k_2' \simeq 1, \qquad (D1)$$

$$L_{\rm k} \simeq \frac{\mu_0 \lambda^2}{d} \left[\frac{2}{\pi} \ln \left(\frac{4}{k_2'} \right) \right]^{-1} \quad \text{for } k_2' \ll k_2 \simeq 1.$$
 (D2)

We are interested in the case where the width of nanostrips is much smaller than the length, $w/\ell_0 \ll 1$, and so we have

$$k'_1 = \sqrt{1 - k_1^2} \simeq 4e^{-\pi\ell_0/2w} \ll 1,$$
 (D3)

$$1 - \gamma^2 \simeq 16e^{-\pi\ell_0/w}\sinh^2\left(\frac{\pi s}{2w}\right),\tag{D4}$$

$$\frac{k_2}{k'_2} = \frac{k_1}{k'_1} (1 - \gamma^2) \simeq 4e^{-\pi\ell_0/2w} \sinh^2\left(\frac{\pi s}{2w}\right), \qquad (D5)$$

from Eqs. (13), (16), and (19). Equation (D5) further reduces to

$$k_2 \simeq e^{-\pi \ell_0 / 2w} (\pi s / w)^2 \ll k'_2 \simeq 1$$
 for $s \ll w$, (D6)

$$k_2 \simeq e^{-\pi(\ell_0/2 - s)/w} \ll k'_2 \simeq 1$$
 for $w < s < \ell_0/2$, (D7)

$$k'_2 \simeq e^{-\pi(s-\ell_0/2)/w} \ll k_2 \simeq 1$$
 for $s > \ell_0/2$. (D8)

Substitution of Eq. (D6) into Eq. (D1), of Eq. (D7) into Eq. (D1), and of Eq. (D8) into Eq. (D2) yields Eqs. (23), (24), and (25), respectively. Note that Eqs. (23) and (24) are expressed as a single form,

$$L_{\rm k} \simeq \frac{\mu_0 \lambda^2}{d} \left\{ \frac{\ell_0}{w} - \frac{4}{\pi} \ln \left[\sinh \left(\frac{\pi s}{2w} \right) \right] \right\} \quad \text{for } s < \ell_0 / 2, \text{ (D9)}$$

which is identical to Eq. (B2).

ACKNOWLEDGMENTS

I thank John R. Clem for stimulating discussions. This work was supported by JSPS KAKENHI Grant Number JP20K05314.

REFERENCES

- ¹C. M. Natarajan, M. G. Tanner, and R. H. Hadfield, Supercond. Sci. Technol. 25, 063001 (2012).
- ²A. J. Kerman, E. A. Dauler, W. E. Keicher, J. K. W. Yang, K. K. Berggren,
- G. Gol'tsman, and B. Voronov, Appl. Phys. Lett. 88, 111116 (2006).
- ³P. K. Day, H. G. LeDuc, B. A. Mazin, A. Vayonakis, and J. Zmuidzinas, Nature (London) **425**, 817 (2003).
- ⁴S. K. Tolpygo, Low Temp. Phys. **42**, 361 (2016).
- ⁵J. R. Clem and K. K. Berggren, Phys. Rev. B **84**, 174510 (2011).
- ⁶J. R. Clem, Y. Mawatari, G. R. Berdiyorov, and F. M. Peeters, Phys. Rev. B **85**, 144511 (2012).
- ⁷R. Meservey and P. M. Tedrow, J. Appl. Phys. **40**, 2028 (1969).
- ⁸K. Yoshida, M. S. Hossain, T. Kisu, K. Enpuku, and K. Yamafuji, Jpn. J. Appl. Phys. **31**, 3844 (1992).
- ⁹A. J. Annunziata, D. F. Santavicca, L. Frunzio, G. Catelani, M. J. Rooks, A. Frydman, and D. E. Prober, Nanotechnology **21**, 445202 (2010).
- ¹⁰J. R. Clem, J. Appl. Phys. **113**, 013910 (2013).
- ¹¹P. M. Hall, Thin Solid Films **1**, 277 (1968).
- ¹²S. K. Tolpygo, E. B. Golden, T. J. Weir, and V. Bolkhovsky, IEEE Trans. Appl. Supercond. **32**, 1400331 (2022).
- ¹³S. K. Tolpygo, E. B. Golden, T. J. Weir, V. Bolkhovsky and R. Rastogi, IEEE Trans. Appl. Supercond. (published online 2023)
- ¹⁴F. B. Hagedorn and P. M. Hall, J. Appl. Phys. **34**, 128 (1963).
- ¹⁵G. Via, C. Navau, and A. Sanchez, J. Appl. Phys. **113**, 093905 (2013).
- ¹⁶G. B. Arfken and H. J. Weber, *Mathematical Methods for Physicists*, 5th ed., (Harcourt, 2001).
- ¹⁷Y. Mawatari, C. Navau, and A. Sanchez, Phys. Rev. B 85, 134524 (2012).
- ¹⁸Y. Mawatari, Supercond. Sci. Technol. **26**, 074005 (2013).
- ¹⁹I. S. Gradshtein and I. M. Ryshik, *Table of Integrals, Series, and Products*, 5th ed. (Academic, 1994).
- ²⁰M. J. Lancaster, Passive Microwave Device Applications of High-Temperature Superconductors, (Cambridge, 1997).
- ²¹C. W. Lam, D. M. Sheen, S. M. Ali, and D. E. Oates, IEEE Trans. Appl. Supercond. 2, 58 (1992).
- ²²K. Enpuku, M. Hoashi, H. Doi, and T. Kisu, Jpn. J. Appl. Phys. **32**, 3804 (1993).
- ²³S. Cho, H. Erlig, A. Z. Kain, H. R. Fetterman, G. -C. Liang, M. E. Johansson, B. F. Cole, and R. S. Withers, Appl. Phys. Lett. 65, 3389 (1998).
- ²⁴T. Dahm and D. J. Scalapino, Appl. Phys. Lett. **69** 4248 (1996).
- ²⁵T. Dahm and D. J. Scalapino, J. Appl. Phys. **81**, 2002 (1997).
- ²⁶J. R. Clem and V. G. Kogan, Phys. Rev. B **86**, 174521 (2012).
- ²⁷E. Brandt and M. Indenbom, Phys. Rev. B 48, 12893 (1993).
- ²⁸E. Zeldov, J. R. Clem, M. McElfresh, and M. Darwin, Phys Rev B 49, 9802 (1994).
- ²⁹M. R. Spiegel, *Theory and Problems of Complex Variables*, (McGraw-Hill, 1981).